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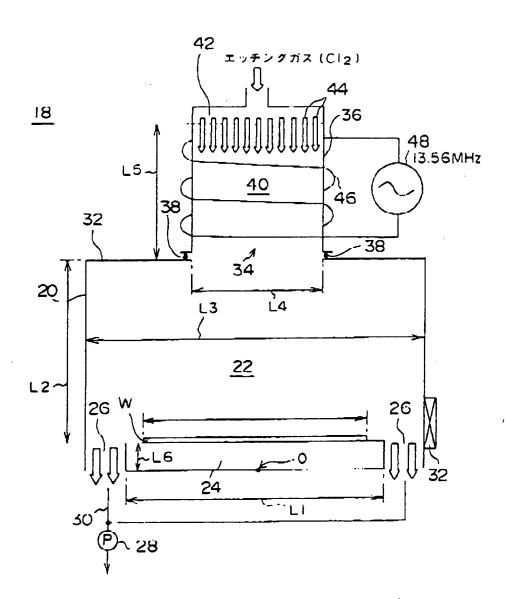
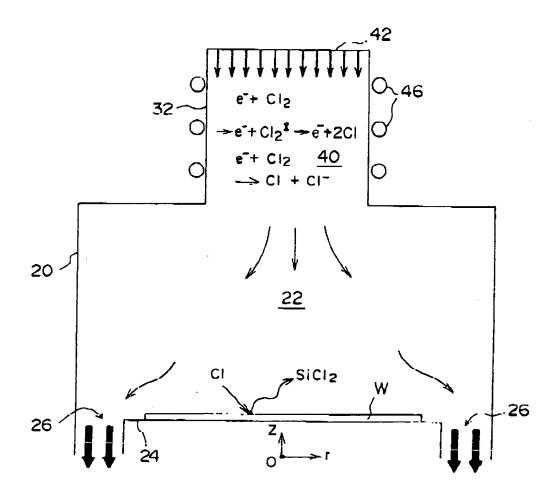


FIG. I



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F1G. 2

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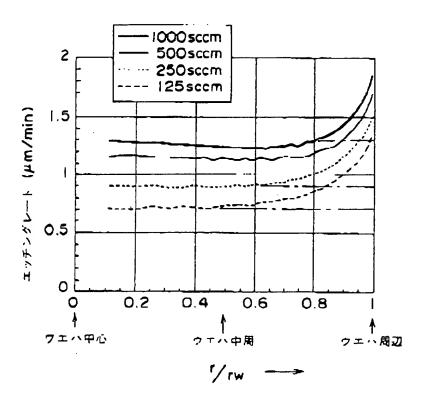
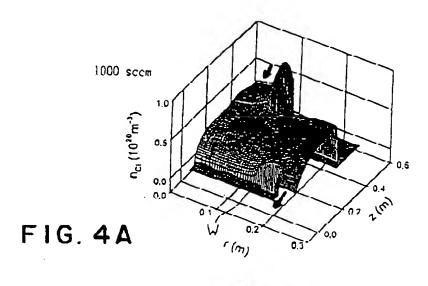
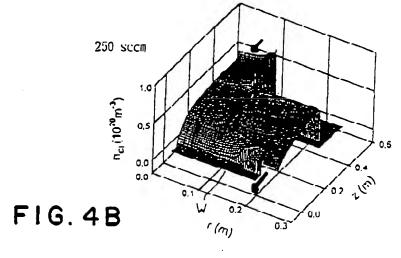
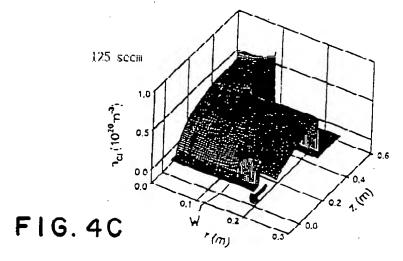


FIG. 3







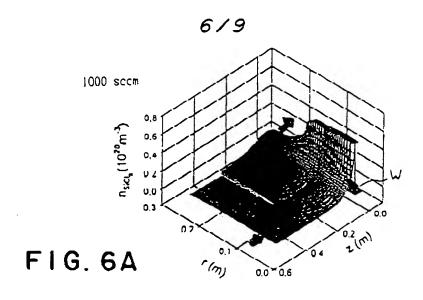


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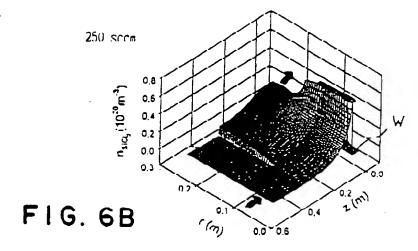
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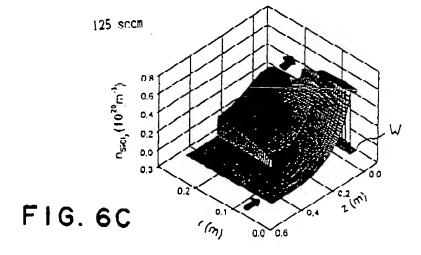
流盘 ·(sccm)	total (Pa)	Cl2(Pa)	CI(Pa)	SiCl2(Pa)
1000	0.447	0.211	0.243	0.0228
500	0.477	0.229	0.226	0.0223
250	0.478	0.201	0.231	0.0459
125	0.479	0.170	0.224	0.0858

F1G. 5

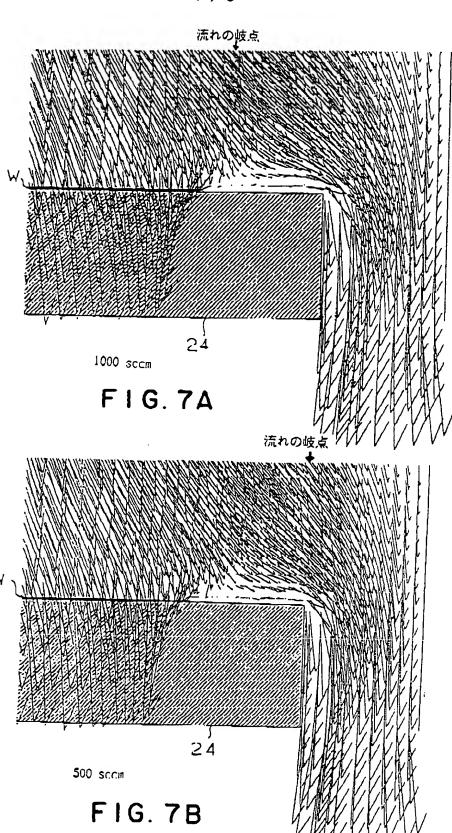


発信: KYOWA PATENT, TKY







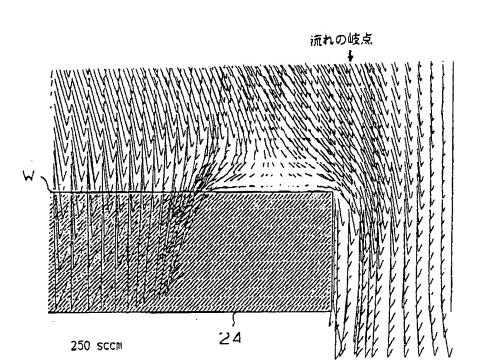


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発信:KYOWA PATENT, TKY



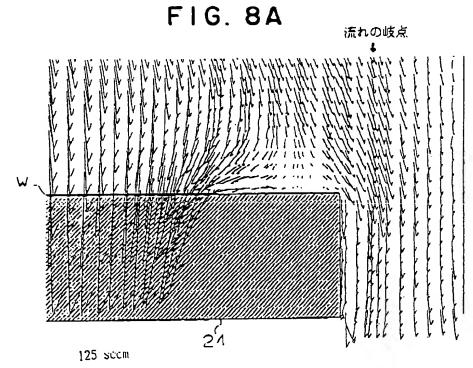


FIG. 8B







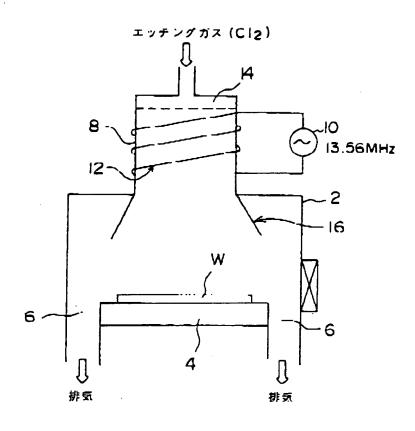


FIG. 9